



A35076-PCT-USA (070050.2713)
PATENT

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s) : James S. Im Customer No. : 21003
Serial No. : 10/525,288 Confirmation No. : 7758
Filed : 02/16/2005 Group Art Unit : 2813
Examiner :
For : Process And System For Laser Crystallization Processing Of Film Regions
On A Substrate To Provide Substantial Uniformity, And A Structure Of
Such Film Regions

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

I hereby certify that this paper is being deposited with the United States
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Name of Person
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David Schalk
Signature

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Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 C.F.R. §§ 1.56 and 1.97(b), applicants bring to the attention of
the Examiner the document listed on the attached Form PTO-1449 and respectfully request
that the listed documents be considered by the Examiner and made of record in the above-
captioned application. Copies of all U.S. Patents and Applications are not enclosed pursuant

to the waiver of 37 CFR 1.98 (a)(2)(i) for all applications filed after June 30, 2003.

03/30/2006 WABDELRI 00000045 024377 10525288

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This submission does not represent that a search has been made or that no better art exists and does not constitute an admission that the listed documents are material or constitute "prior art." If the Examiner applies the documents as prior art against any claim in the application and applicants determine that the cited documents do not constitute "prior art" under United States law, applicants reserve the right to present to the Office the relevant facts and law regarding the appropriate status of the documents.

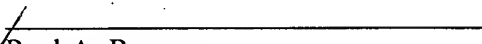
Applicants further reserve the right to take appropriate action to establish the patentability of the disclosed invention over the listed documents, should the documents be applied against the claims of the present application.

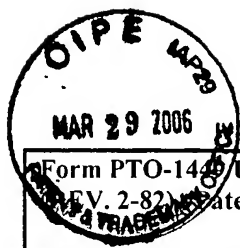
Applicants have enclosed the required fee of \$180.00 due in connection with this. If any additional fee is due, or if any overpayment has been made, the Commissioner is authorized to charge any such fee or credit any overpayment, to our Deposit Account No. 02-4377.

Respectfully submitted,

BAKER BOTTS L.L.P.



By: 
Paul A. Ragusa
Patent Office Reg. No. 38,587
30 Rockefeller Plaza
44th Floor
New York, NY 10012-4498
Attorney for Applicants
212-408-2500



Form PTO-1449 U.S. Department of Commerce Patent and Trademark Office INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Atty. Docket No. A35760-PCT-USA (070050.2713)	Serial No. 10/525,288
	Applicant James S. Im	
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U.S. PATENT DOCUMENTS

Exam. Initial.	No.	Document No.	Issue/Publication Date	Applicant(s)
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	2.	4234358	11/18/1980	Celler et al.
	3.	4309225	01/05/1982	Fan et al.
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	15.	4970546	11/1990	Suzuki et al.

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Exam Initial	No.	Document No.	Publication Date	Country	Translation
					Yes No
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	103.	2338342	12/15/1999	GB	
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	105.	6252048	09/09/1994	JP	<u>No</u>
	106.	6283422	10/07/1994	JP	<u>No</u>
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					Yes	No
	113.	9931719	06/24/1999	WO		<u>No</u>
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	127.	04017382	02/26/2004	WO		
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					Yes	No
	129.	04017380	02/26/2004	WO		
	130.	04075263	08/19/2003	WO		

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	160.	T. Noguchi, "Appearance of Single-Crystalline Properties in Fine-Patterned Si Thin Film Transistors (TFTs) by Solid Phase Crystallization (SPC)," Jpn. J. Appl. Phys. Vol. 32 (1993) L1584-L1587
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